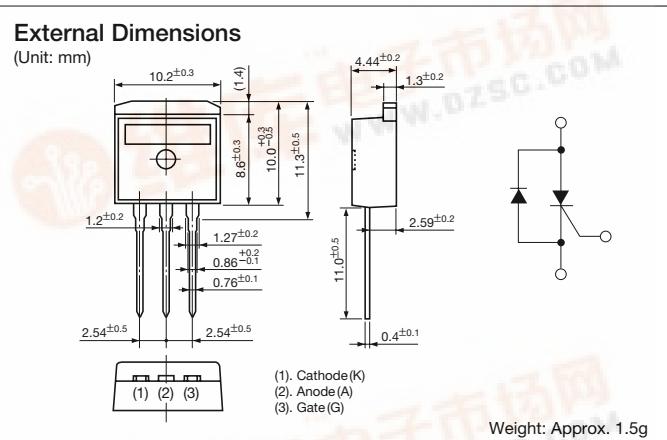


# TO-220S Thyristor with built-in reverse diode for HID lamp ignition

## TFC561D

### ■ Features

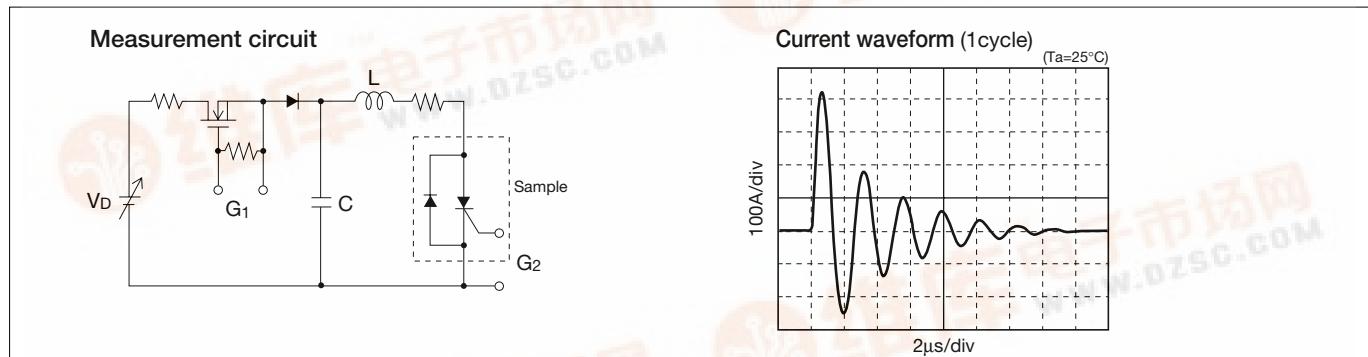
- Repetitive peak off-state voltage:  $V_{DRM}=600V$
- Repetitive peak surge on-state current:  $I_{TRM}=430A$
- Critical rate-of-rise of on-state current:  $di/dt=1200A/\mu s$
- Gate trigger current:  $I_{GT}=20mA$  max
- With built-in reverse diode



### ■ Absolute Maximum Ratings

| Parameter                                   | Symbol      | Ratings     | Unit       | Conditions  |
|---|-------------|-------------|------------|---|
| Repetitive peak off-state voltage           | $V_{DRM}$   | 600         | V          | $T_j=-40$ to $+125^\circ C$ , $R_{GK}=1k\Omega$                   |
| Repetitive surge peak on-state current      | $I_{TRM}$   | 430         | A          | $V_D \leq 430V$ , 100kcycle, $W_p=1.3\mu s$ , $T_a=125^\circ C$ * |
| Critical rate-of-rise of on-state current   | $di/dt$     | 1200        | $A/\mu s$  | *   |
| Peak forward gate current                   | $I_{FGM}$   | 2.0         | A          | $f \geq 50Hz$ , duty $\leq 10\%$                                  |
| Peak gate power loss                        | $P_{GM}$    | 5.0         | W          | $f \geq 50Hz$ , duty $\leq 10\%$                                  |
| Average gate power loss                     | $P_{G(AV)}$ | 0.5         | W          |   |
| Peak reverse gate voltage                   | $V_{RGM}$   | 5           | V          | $f \geq 50Hz$   |
| Diode repetitive peak surge forward current | $I_{FRM}$   | 240         | A          | $V_D \leq 430V$ , 100kcycle, $W_p=1.3\mu s$ , $T_a=125^\circ C$ * |
| Junction temperature                        | $T_j$       | -40 to +125 | $^\circ C$ |   |
| Storage temperature                         | $T_{stg}$   | -40 to +125 | $^\circ C$ |   |

\* The surge current for  $T=10ms$  /cycle shall be applied 50 cycles successively, and an interval time shall follow to cool down the junction temperature of the device to  $125^\circ C$ . This process shall be repeated up to 100K cycles.



### ■ Electrical Characteristics

( $T_j=25^\circ C$ )

| Parameter                | Symbol       | Ratings |      |     | Unit         | Conditions   |
|--------------------------|--------------|---------|------|-----|--------------|--|
|                          |              | min     | typ  | max |              |  |
| On-state voltage         | $V_{TM}$     |         |      | 1.4 | V            | $I_T=10A$  |
| Gate trigger voltage     | $V_{GT}$     |         |      | 1.5 | V            | $V_D=6V$ , $R_L=10\Omega$                              |
| Gate trigger current     | $I_{GT}$     |         |      | 20  | mA           | $V_D=6V$ , $R_L=10\Omega$                              |
| Gate non-trigger voltage | $V_{GD}$     | 0.1     |      |     | V            | $V_D=480V$ , $T_j=125^\circ C$                         |
| Holding current          | $I_H$        | 2       | 10.0 |     | mA           | $R_{G-K}=1k\Omega$ , $T_j=25^\circ C$                  |
| Off-state current (1)    | $I_{DRM}(1)$ |         |      | 100 | μA           | $V_D=V_{DRM}$ , $R_{G-K}=1k\Omega$ , $T_j=25^\circ C$  |
| Off-state current (2)    | $I_{DRM}(2)$ |         |      | 1   | mA           | $V_D=V_{DRM}$ , $R_{G-K}=1k\Omega$ , $T_j=125^\circ C$ |
| Thermal resistance       | $R_{th}$     |         |      | 4.0 | $^\circ C/W$ | Junction to case                                       |
| Diode forward voltage    | $V_F$        |         |      | 1.4 | V            | $I_F=10A$  |